# 2SC4096

# Silicon NPN triple diffusion planar type

For high breakdown voltage high-speed switching

### Features

- High-speed switching
- ullet High collector to base voltage  $V_{CBO}$
- Wide area of safe operation (ASO)
- Satisfactory linearity of foward current transfer ratio h<sub>FE</sub>

## Absolute Maximum Ratings (T<sub>C</sub>=25°C)

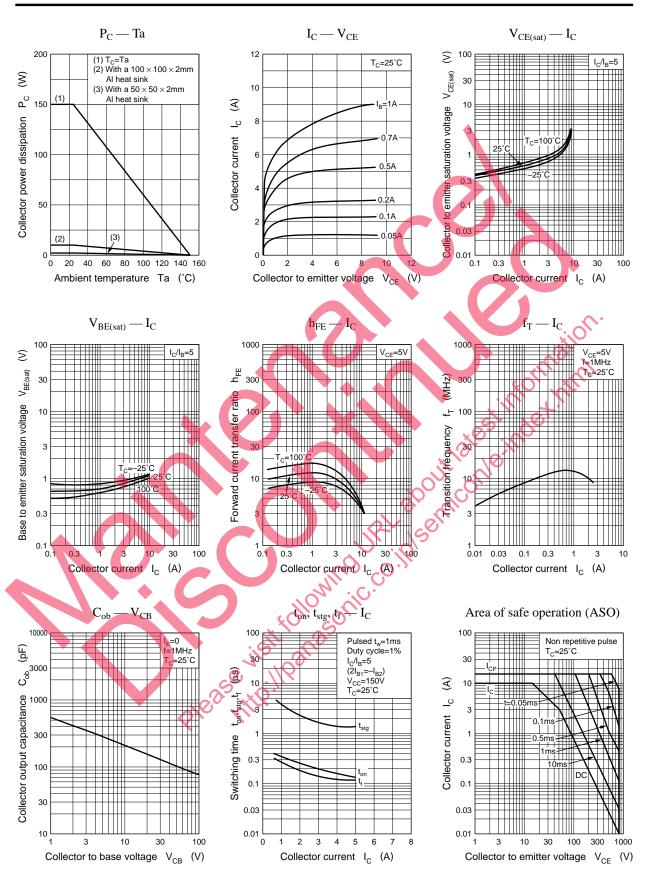
Parameter		Symbol	Ratings	Unit
Collector to base voltage		V <sub>CBO</sub>	1400	V
Collector to emitter voltage		V <sub>CEO</sub>	800	V
Emitter to base voltage		V <sub>EBO</sub>	7	V
Peak collector current		$I_{CP}$	15	A
Collector current		I <sub>C</sub>	10	A
Base current		$I_{\mathrm{B}}$	5	A
Collector power	T <sub>C</sub> =25°C		150	
dissipation	Ta=25°C	$P_{C}$	3.5	W
Junction temperature		$T_{j}$	150	°C
Storage temperature		T <sub>stg</sub>	-55 to +150	°C

# Unit: mm \$\frac{\quad 3.3\dot 0.2}{5.0\dot 0.3} \\ \frac{\quad 3.3\dot 0.2}{5.0\dot 0.3} \\ \frac{\quad 3.0}{3.0} \\ \quad 3.0} \\ \frac{\quad 3.0}{3.0} \\ \quad 3.0} \\ \qua

# Electrical Characteristics (T<sub>C</sub>=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	$I_{CBO}$	$V_{\rm CB} = 1400  \text{V},  I_{\rm E} = 0$			100	μА
Emitter cutoff current	I <sub>EBO</sub>	$V_{EB} = 7V, I_{C} = 0$			100	μА
Collector to emitter voltage	V <sub>CEO</sub>	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0$	800			V
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = 5V$ , $I_C = 5A$	5		15	
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 5A, I_B = 1A$			5	V
Base to emitter saturation voltage	V <sub>BE(sat)</sub>	$I_C = 5A, I_B = 1A$			1.5	V
Transition frequency	$f_T$	$V_{CE} = 5V, I_{C} = 1A, f = 1MHz$		13		MHz
Turn-on time	t <sub>on</sub>	$I_C = 5A$ , $I_{B1} = 1A$ , $I_{B2} = -2A$ ,		1.0		μs
Storage time	t <sub>stg</sub>			3.5		μs
Fall time	t <sub>f</sub>	$V_{CC} = 250V$		0.3		μs

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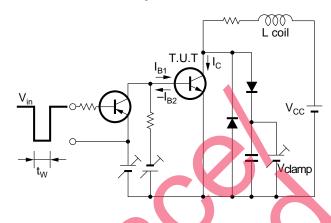
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### Area of safe operation, reverse bias ASO

# $\begin{array}{l} {\sf L_{coil}}{=}100\mu{\sf H} \\ {\sf I_C/I_{B1}}{=}5 \\ ({\sf I_{B1}}{=}{-}{\sf I_{B2}}) \\ {\sf T_C}{=}25^{\circ}{\sf C} \end{array}$ 3 15 \_ပ Collector current 10 200 400 600 800 1000 1200 1400 1600

Collector to emitter voltage  $V_{CE}$  (V)

### Reverse bias ASO measuring circuit





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